

FEATURES

- Visible light response
- Sintered construction
- Low cost

DESCRIPTION

The **PDV-P9008** are (CdS), Photoconductive photocells designed to sense light from 400 to 700 nm. These light dependent resistors are available in a wide range of resistance values. They're packaged in a two leaded plastic-coated ceramic header.

APPLICATIONS

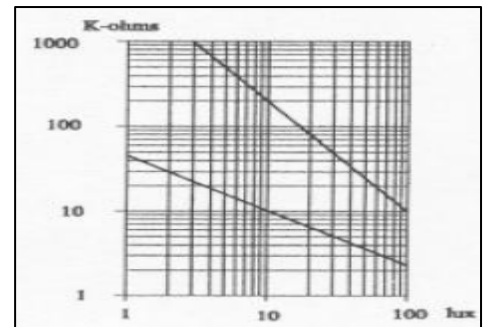
- Camera exposure
- Shutter controls
- Night light Controls



ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{pk}	Applied Voltage		150	V
P _{d Δpo/Δt}	Continuous Power Dissipation		125	mW/°C
T _O	Operating and Storage Temperature	-25	+75	°C
T _S	Soldering Temperature*		+260	°C

* 0.200 inch from base for 3 seconds with heat sink.



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _D	Dark Resistance	After 10 sec. @ 10 Lux @ 2856 °K	20			MΩ
R _I	Illuminated Resistance	10 Lux @ 2856 °K	10		200	KΩ
S	Sensitivity	$\frac{\text{LOG}(R_{100})-\text{LOG}(R_{10})^{**}}{\text{LOG}(E_{100})-\text{LOG}(E_{10})^{***}}$		0.85		Ω/Lux
λ _{range}	Spectral Application Range	Flooded	400		700	nm
λ _{peak}	Spectral Application Range	Flooded		570		nm
t _r	Rise Time	10 Lux @ 2856 °K		60		ms
T _f	Fall Time	After 10 Lux @ 2856 °K		25		ms

**R₁₀₀, R₁₀: cell resistances at 100 Lux and 10 Lux at 2856 °K respectively .

***E₁₀₀, E₁₀: luminances at 100 Lux and 10 Lux 2856 °K respectively.

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